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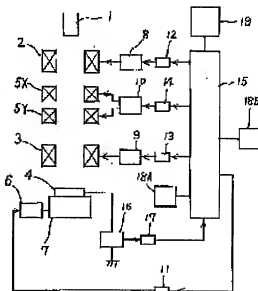
ONO MIYUKI

(54) METHOD FOR INSPECTING HOLE BY USING CHARGED PARTICLE BEAM

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method for inspecting the etching state of a contact hole or a via hole.

SOLUTION: Electron beams are sequentially irradiated to a contact hole formed on a sample like a wafer, and an absorption current flowing in the sample 4 is detected by a current amplifier 16, and obtained absorption current signal data is stored in a memory 18. A controller 15 checks the absorption current signal data up in a relation between a current flowing between the sample and a ground to be acquired in advance by use of a standard sample and an etching depth of a substrate in the contact hole, and inspects the etching depth of the substrate in a hole to be measured.



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